

Characterization and performance of multi-pixel photon counters in T2K experiment

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MPPC (Multi-Pixel Photon Counter) Multi-pixel Geiger mode photodiode

26 x 26 pixel array, 9 pixels occupied by an electrode



Bias voltage is larger than the breakdown value but no current through a diode until first carrier arrives in the p-n junction area. Geiger avalanche is quenched by a voltage drop across R_{quench}

Hamamatsu type :	S10362-13-50C
Number of pixels :	667
Pixel size :	50 x 50 μm²
Total sensitive area :	1.3 x 1.3 mm ²
Operational bias voltage :	~70 V
Operational overvoltage ΔV	: ~ 1.3 V
PDE at 520 nm (ΔV =1.3 V):	~ 28 %
Gain at ΔV =1.3 V :	0.75 x 10 ⁶
Dark rate (thr=0.5 pe) :	0.5 – 1.2 MHz
Recovery time $ au$:	13.4 ns
Optical crosstalk :	9 – 12 %
Afterpulsing :	14 – 16 %
V _{breakdown} temp. coefficient:	52 ± 4 mV/de





T2K is a long base-line neutrino oscillation experiment. Near detector complex ND280 is built at a distance of 280 m from the target.





PDE is about 25% for average emission spectrum of Kuraray Y11 fiber at overvoltage $\Delta V=1.3$ V.

PDE depends almost linearly on ΔV within operational range of 1.0-1.6 V. No temperature dependence at a fixed ΔV .



First large scale application of multi-pixel Geiger mode photodiodes MPPCs

ND280 scintillator detectors N	umber of channels
 Fine-Grained Detector (FGD) – tracker : Electromagnetic Calorimeter (ECAL) : Pi-Zero Detector (P0D) – π⁰ detector : SMRD – muon detector within magnet yoke gaps INGRID – on-axis neutrino beam monitor : 	8448 MPPCs 22336 MPPCs 10400 MPPCs 4016 MPPCs 10796 MPPCs

Parameters of MPPC

contributions from crosstalk, afterpulsing, etc.

Quality Assurance and Failure Rate



Step 1. Tests of MPPCs by Hamamatsu

Development of MPPCs by Hamamatsu started in 2005. The mass production for T2K has started in February 2008.

Hamamatsu tested all MPPCs before shipping them to T2K. The plots show the dark rate and bias voltage distributions among 53800 MPPCs at 25°C. Hamamatsu has specified the bias voltages to have the same gain of 7.5×10^5 for each MPPC.

Step 2. All MPPCs were tested by T2K groups



MPPCs were irradiated by LED pulser. Measured parameters include breakdown voltage value, gain, dark rate, light output at 25°C. Each T2K group had set the own

T2K groups	Tested MPPCs	Rejected MPPCs
Kyoto (Japan)	17695	9
CSU (USA)	11500	14
LSU (USA)	1717	11
LLR (France)	3158	0
Warwick (England)	1820	0
ICL (England)	1897	0
T. U. Warsaw (Poland)	1202	4



MPPC gain can be defined as the charge produced in a single pixel avalanche: $G = C_{pix}^* \Delta V$.

Overvoltage ΔV is calculated by: $\Delta V = V_{\text{bias}} - V_{\text{breakdown}}$ V_{bias} is supply voltage, V_{breakdown} is the measured parameter.

No gain vs temperature dependence at a fixed ΔV .

Dark rate

Dark rate consists mainly of single pixel avalanche pulses caused by thermal generation. Larger amplitudes are generated by optical crosstalk and afterpulsing.

Dark rate for MPPC samples is distributed in range 0.5–1.2 MHz at t = 25° C and $\Delta V = 1.4$ V

propagated in the neighboring pixels.

2.5 Dark

- 0 0 0 0 0

2.5

 $\Delta V (V)$

 $\nabla \Delta V = 0.9V$

 $\Delta V = 1.1 V$

 $\Delta \Delta V = 1.3V$

 $\Box \Delta V = 1.5V$

 $\triangleleft \Delta V = 1.7V$

20

30

Afterpulsing is caused by the

carriers within the same pixel

trapping and late releasing of charge

Crosstalk and afterpulsing Crosstalk is caused by optical photons generated in an avalanche and 1p.e.

40

Temperature (°C)

50



rejection criterion.

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Average rejection rate is 0.1%

Failure in readout of a channel

includes all possible reasons:

MPPC failure rate is less than

MPPC, cabling, front-end

the presented numbers.

electronics.

MPPC failure rate in beam runs (December 2009 – March 2011)

Detector	Number of MPPCs	Failed channels	Fraction
INGRID	10796	18	0.17 %
P0D	10400	7	0.07 %
FGD	8448	20	0.24 %
SMRD	4016	7	0.17 %
DS ECAL	3400	11	0.32 %

First T2K result on June 15, 2011: $\rightarrow v_{e}$ appearance -Indication for



Combined crosstalk and afterpulse probability is shown in the plot vs overvoltage ΔV . The probability is fitted : $P = 0.094*\Delta V^2$ (within operational range of 0.5–1.6 V)

Independent measurements also yielded: Afterpulse probability $P = 0.08 \Delta V^2$ Crosstalk probability $P = (0.05 - 0.08)^* \Delta V^2$

References

x 10[°]

.≥ ^{0.7}

es 0.5 0.4

▼ T = 0°C

T = 10°C

▲ T = 20°C

□ T = 30°C

◄ T = 40°C

• T = 50°C

 ∇ T = 0°C ♦ T = 10°C

▲ T = 20°C

T = 30°C

◄ T = 40°C

• T = 50°C

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